NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV99** is a Common Emitter Device Designed for Amplifier Applications up to 860 MHz.

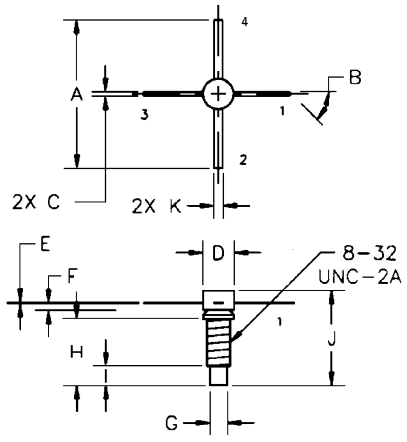
FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- High Gain

MAXIMUM RATINGS

I_C	300 mA
V_{CBO}	45 V
V_{CEO}	25 V
V_{EBO}	3.5 V
P_{DISS}	5.3 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °Cto +150 °C
θ_{JC}	33 °C/W

PACKAGE STYLE 205 4L STUD



1 = COLLECTOR 2 & 4 = EMITTER
3 = BASE

DIM	MILLIMETER	TOL	INCHES	TOL
A	25.40	.38	1.000	.015
B	45°	5°	45°	5°
C	0.76	.13	.030	.005
D	5.18 DIA	.13	.204 DIA	.005
E	1.19	.13	.047	.005
F	0.13	.02	.005	.001
G	2.92	.13	.115	.005
H	12.83	.38	.505	.015
I	3.30	.13	.130	.005
J	16.18	REF	.637	REF
K	1.52	.13	.060	.005

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 1.0mA	45			V
BV_{CER}	I_C = 10 mA R_{BE} = 10 Ω	45			V
BV_{EBO}	I_E = 1.0 mA	3.5			V
I_{CBO}	V_{EB} = 5.0 V			1.0	mA
h_{FE}	V_{CE} = 5 V I_C = 100 mA	20			---
C_{OB}	V_{CB} = 24 V f = 1.0 MHz			3.5	pF
P_G	V_{CE} = 20 V I_C = 150 mA f = 860 MHz	12			dB
IMD_1	V_{CE} = 20 V I_C = 150 mA f = 860 MHz P_{out} = 0.5 W	-58			dBc

Specifications are subject to change without notice.